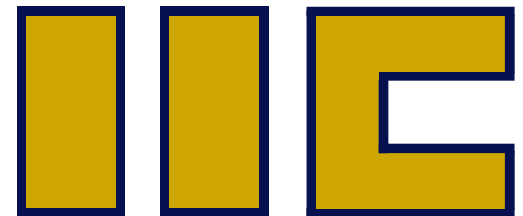


# Quilt Packaging® For Power Electronics

*21 March 2013*

Jason M. Kulick  
President, Co-Founder  
Indiana Integrated Circuits, LLC



Indiana Integrated Circuits<sub>LLC</sub>

# Overview

- Introduction
- Quilt Packaging (QP) technology
  - Concept
  - Examples
  - Advantages
  - QP progress in power

# Indiana Integrated Circuits, LLC (IIC)

Formed to commercialize QP

- Located in South Bend, IN
- Licensing/prototyping biz model
- Successive funding rounds through Series A (8/2012)
- Steady growth in QP & R&D

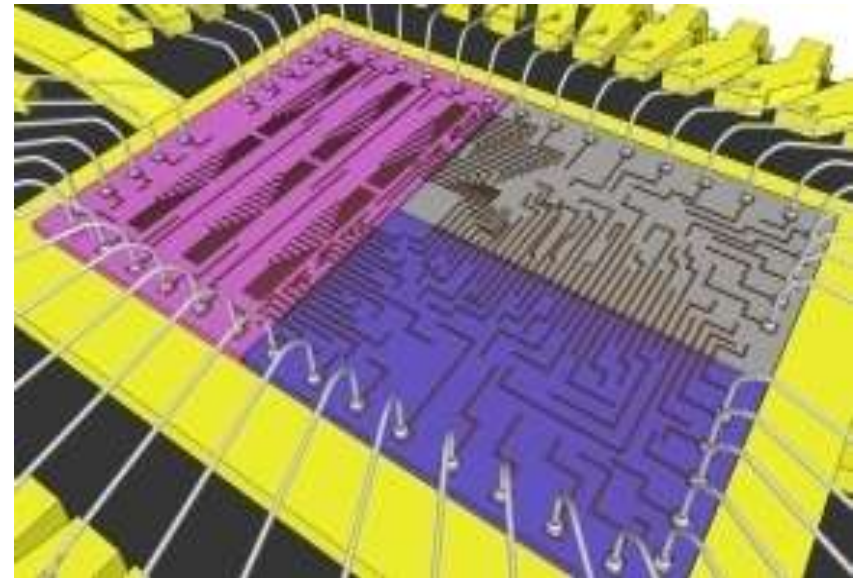
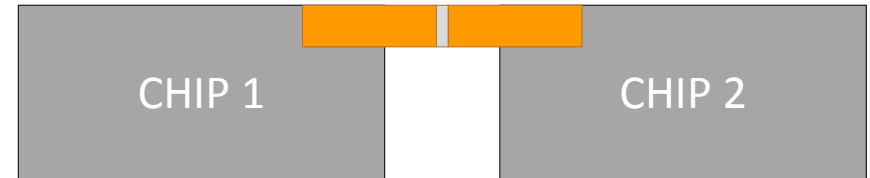
Contract R&D Experience:

- E-Beam Lithography
- Specialty Plating
- DRIE & ICP etching
- IC & MEMs prototyping
- Magnetics/nanomagnetic fabrication & testing



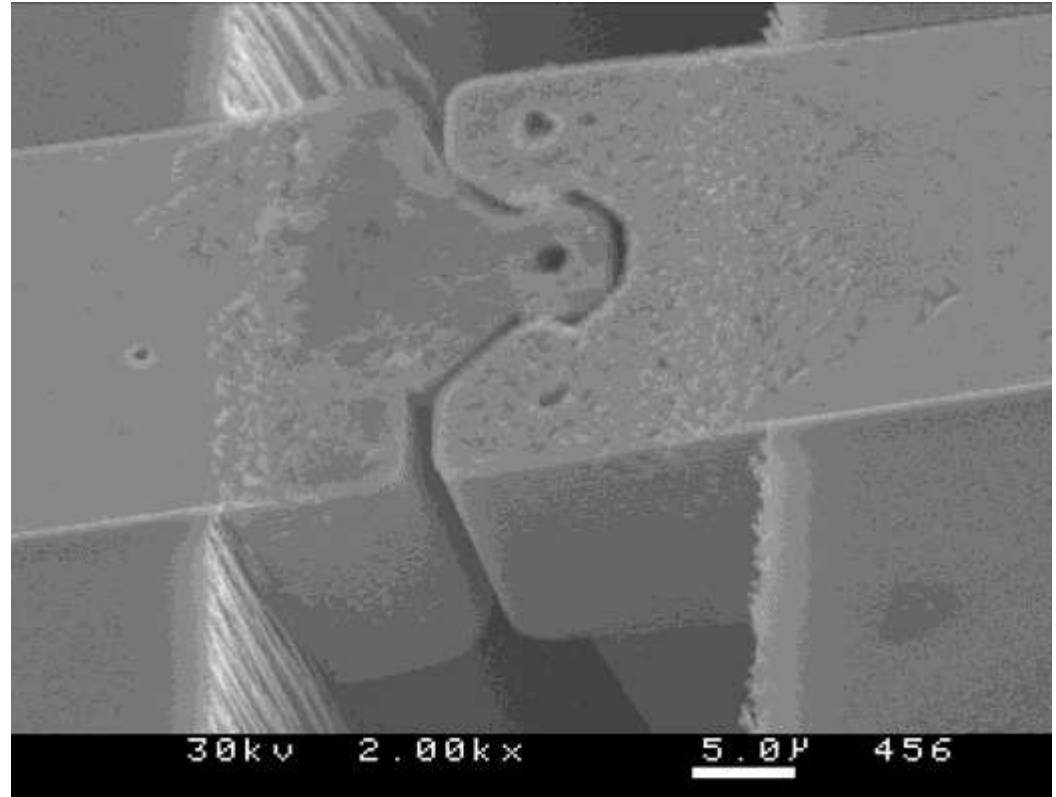
# Quilt Packaging (QP) Technology

- Edge-connections joined to create multi-chip “quilt,” developed at Notre Dame
- “Monolithic” assemblies from same or disparate materials & process technologies
- Extremely low impedances
- Enables optimization for cost and functionality
- Industry-standard tools and fabrication processes

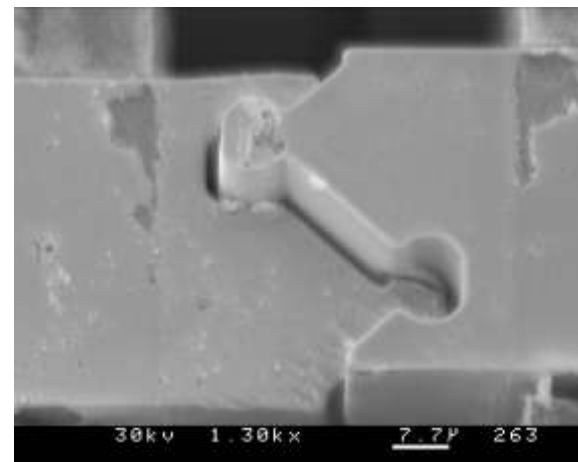
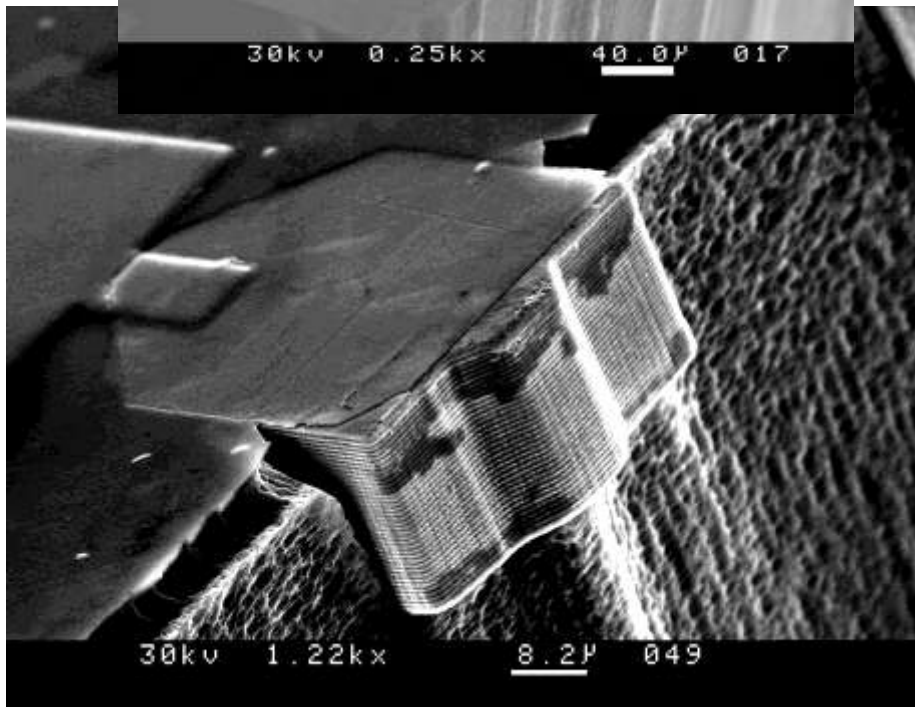
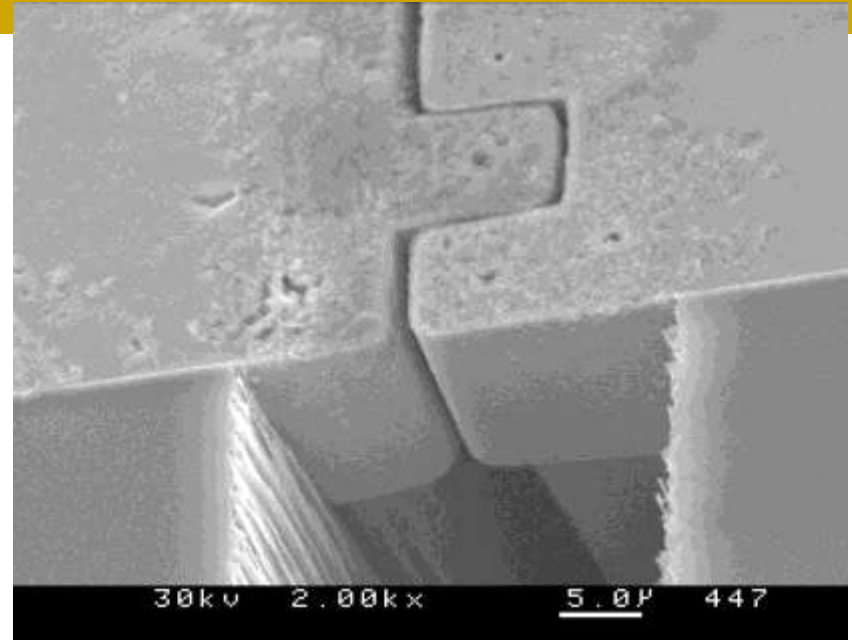
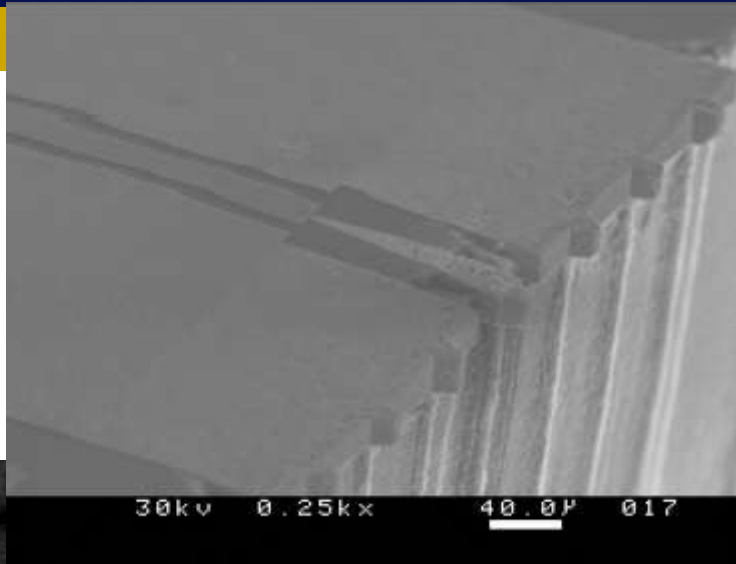


# QP-Interconnect Structures

- Edge connection structures called “nodules”
- Solid metal, typically 10-200  $\mu\text{m}$  wide,  $\sim 20\text{-}50$   $\mu\text{m}$  thick
- Customizable shapes-including interlocking-enables sub-micron chip alignment



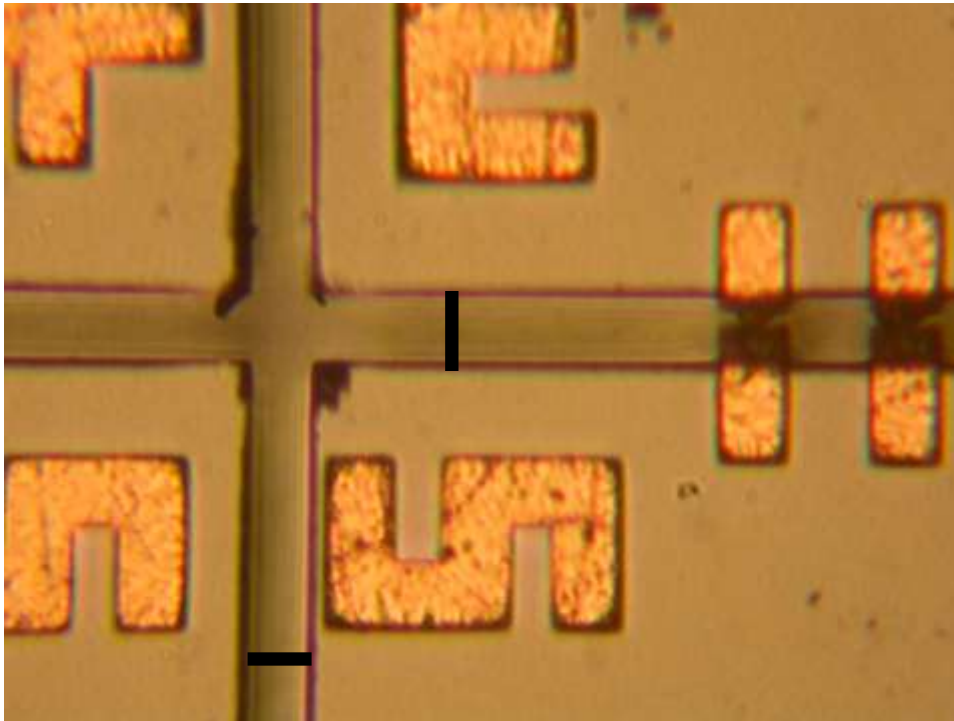
# QP Customizable I/O



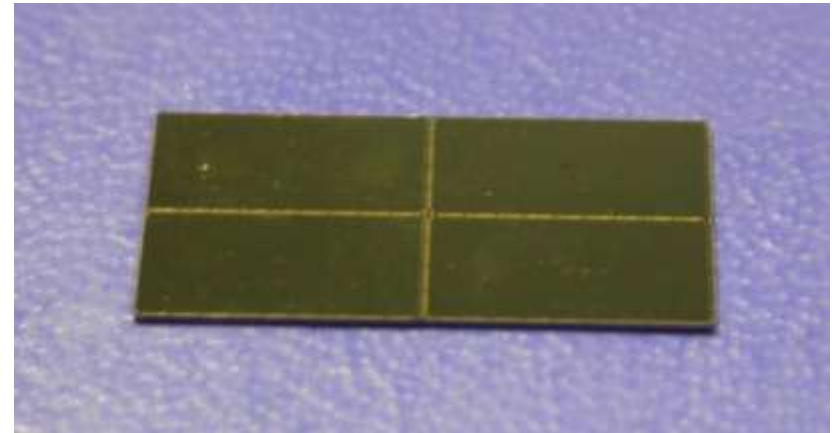
Indiana Integrated Circuits, LLC



# Sub-Micron Chip Alignment



— = 30 micron



Interior (left) of four-chip quilt (above)

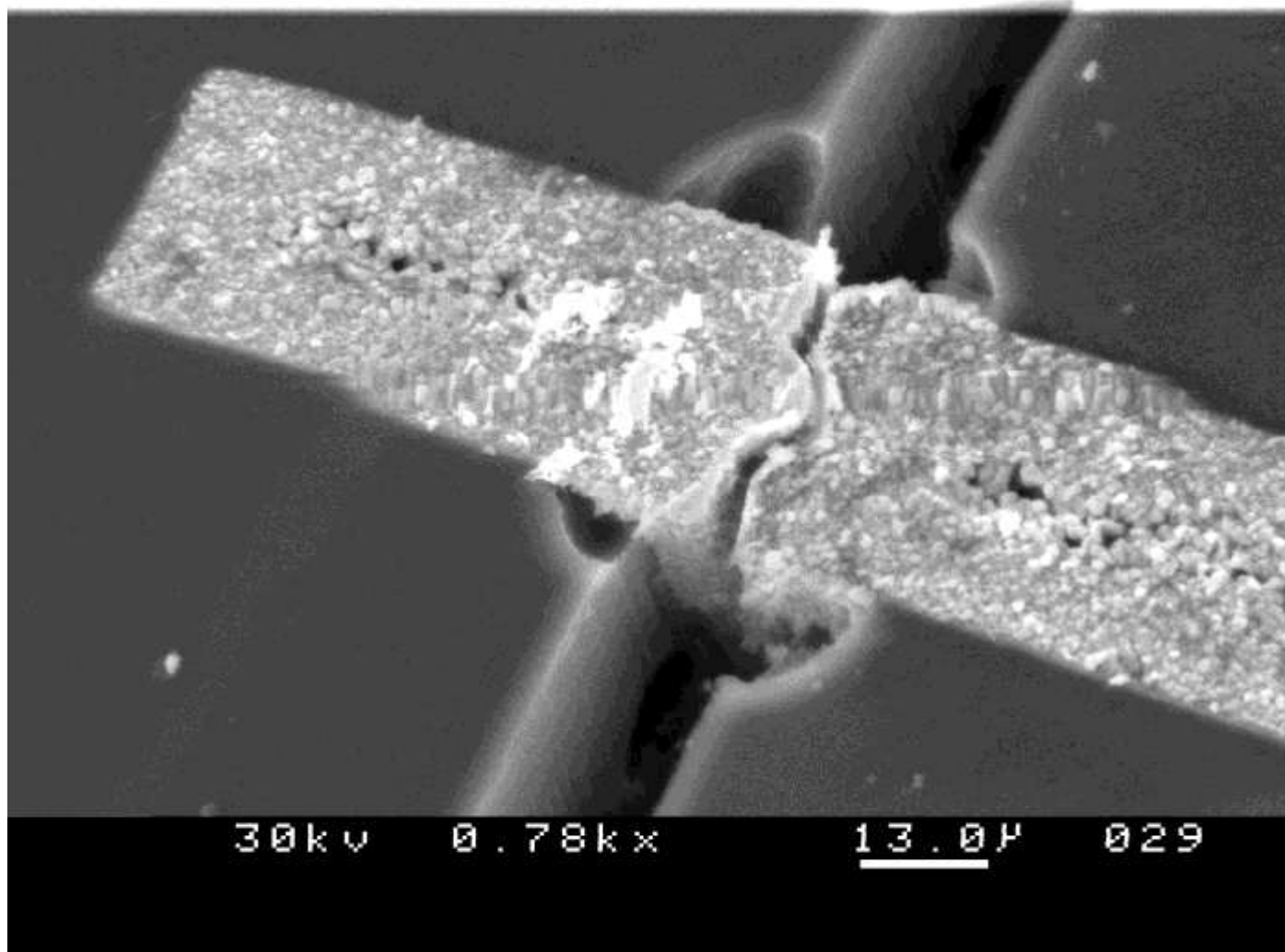
QP enable extremely accurate alignment

# Si QP 2x2 Array (1 in<sup>2</sup> chips)



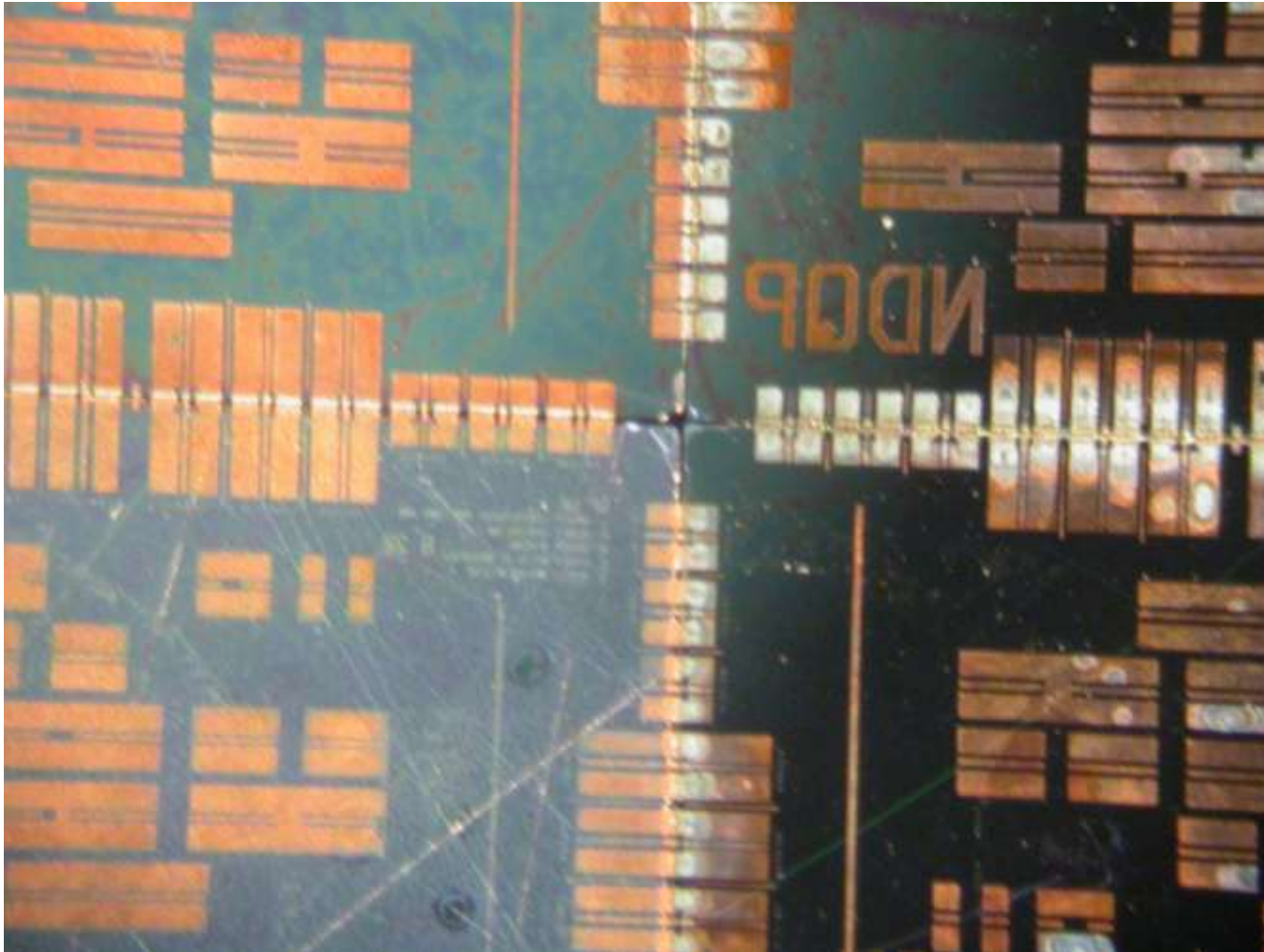


# ~15 um gap post-solder

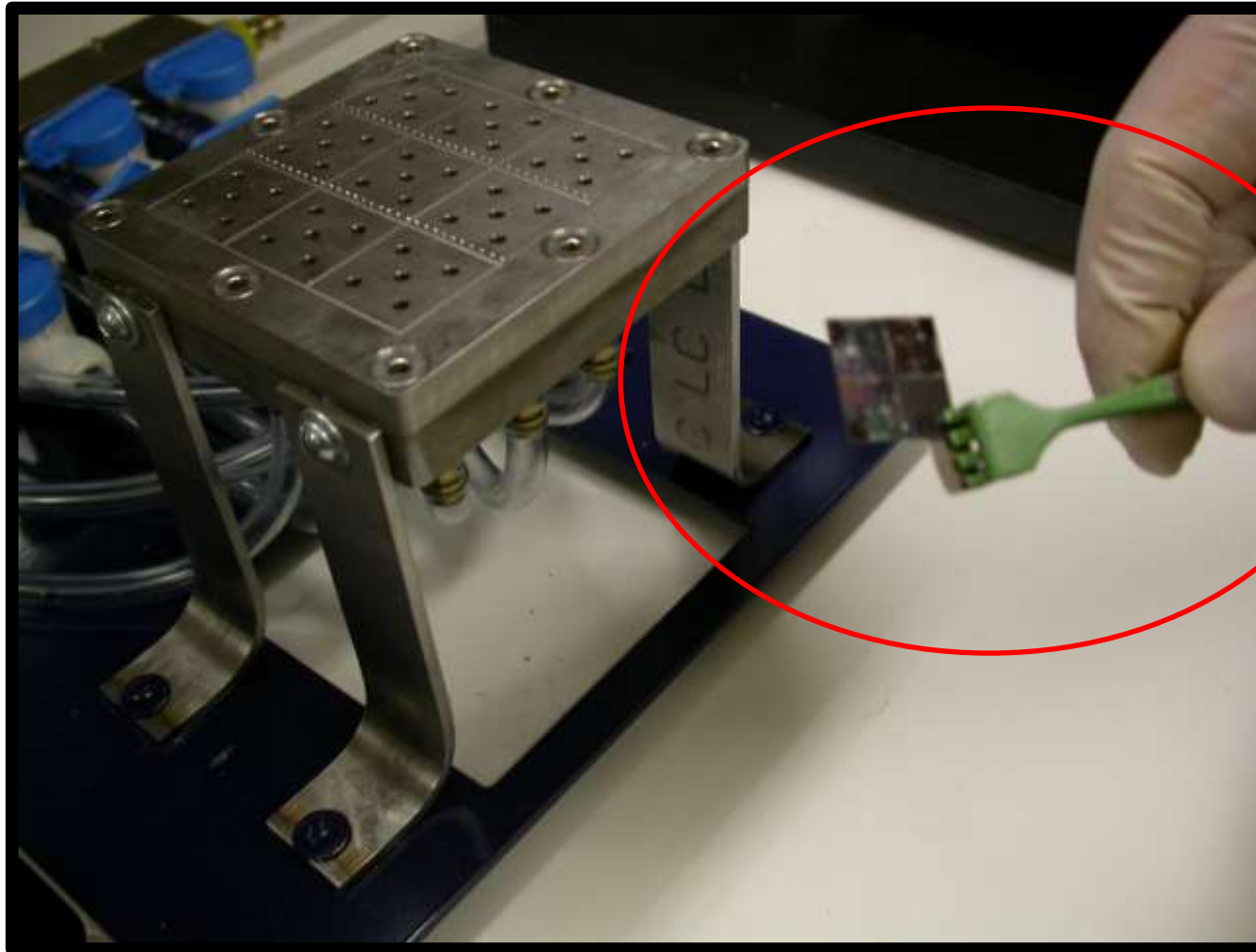


Indiana Integrated Circuits, LLC

# Inner seam of 4-chip Si test quilt

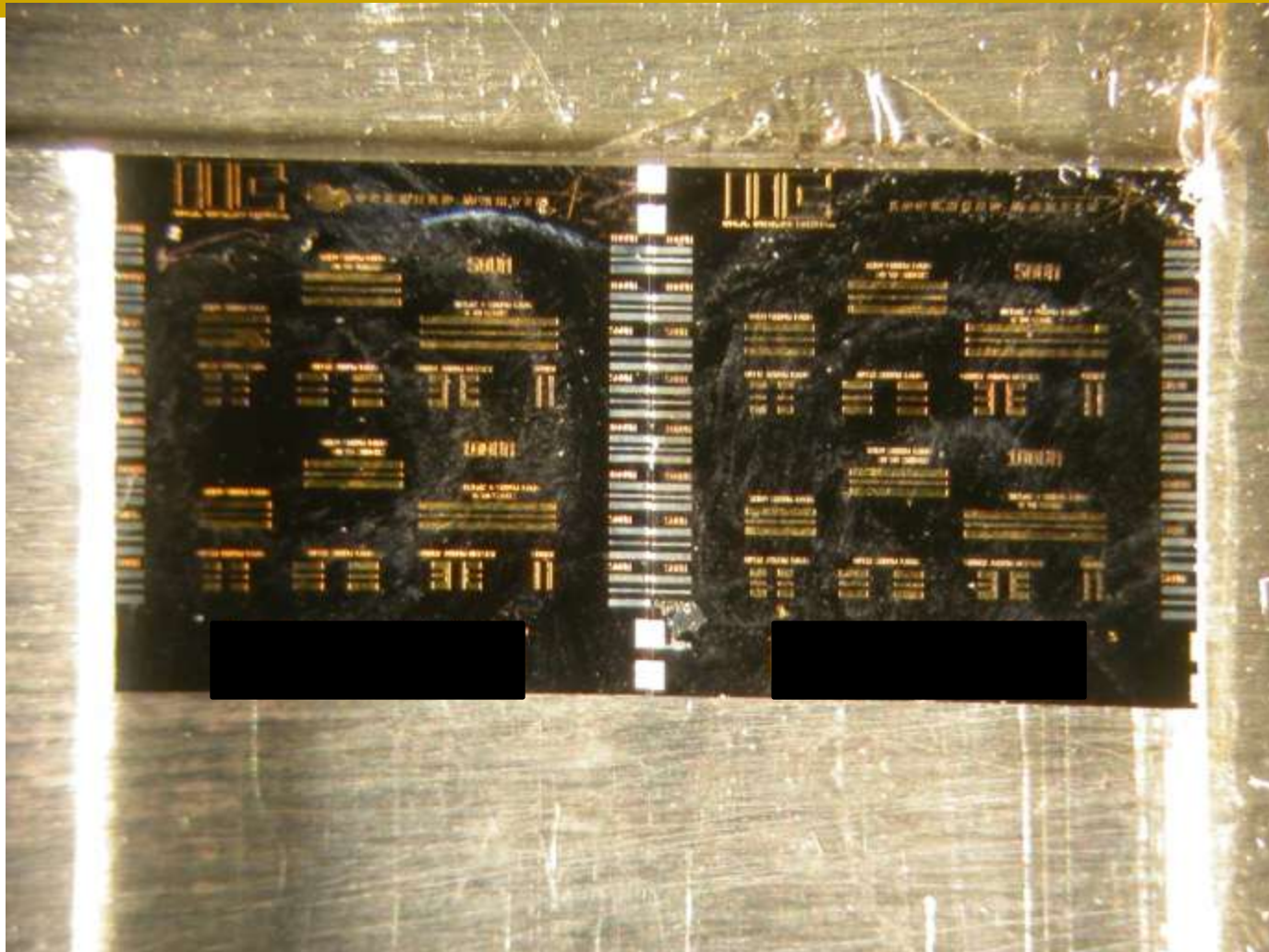


# 4-chip quilt mechanically strong

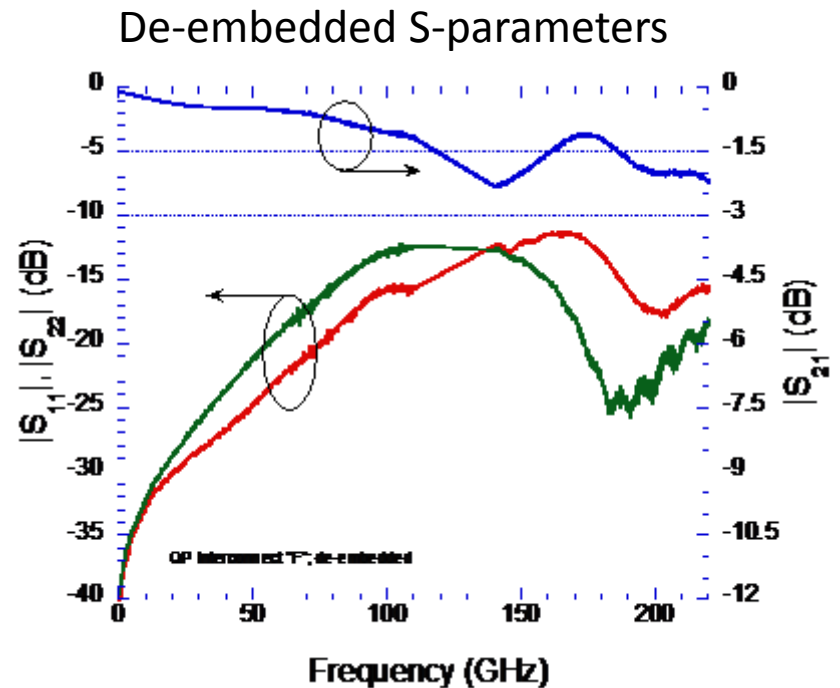
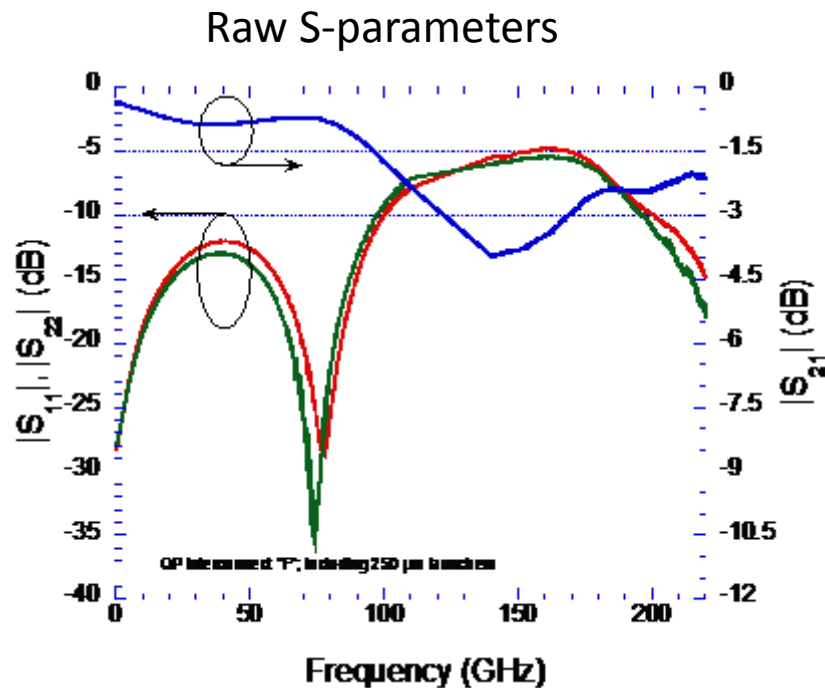




# GaAs QP Chipset

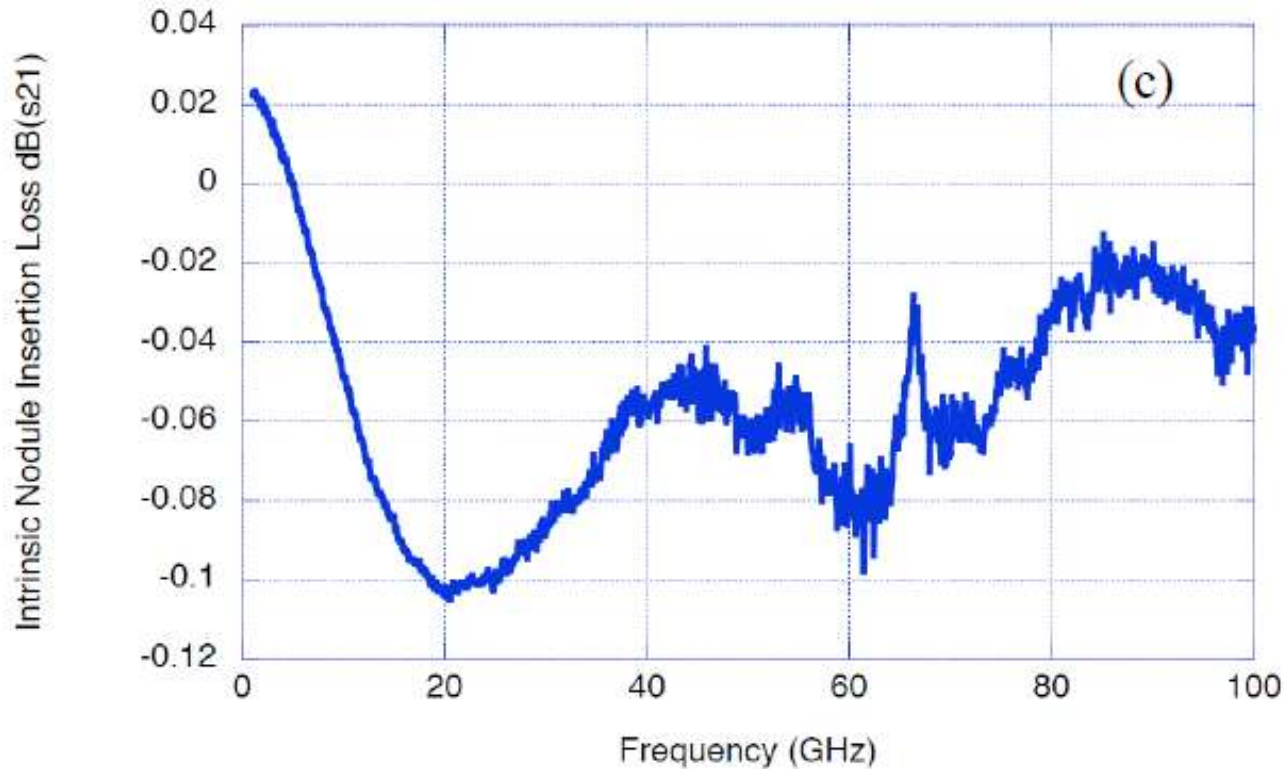


# GaAs Measurement Data Sample



**\*Less than 3 dB insertion loss at 220 GHz**

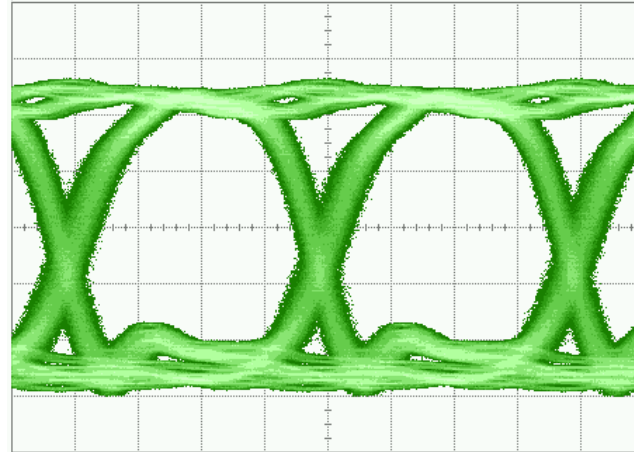
# QP Microwave Performance



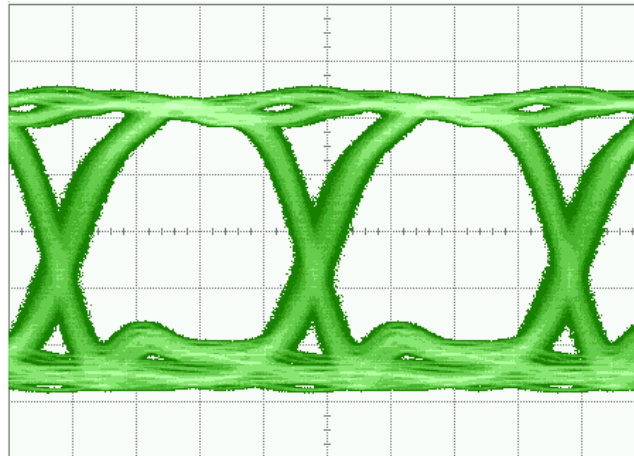
Less than 0.1 dB insertion loss from 50 MHz past 100 GHz, with no resonances. Recent unpublished results under 0.9 dB at 180 GHz

# QP Eye diagrams

- Measurement of 12 Gb/s eye pattern (Anritsu MP1763B)
  - Horiz. 100 mV/div
  - Vert. 20 ps/div
- Data stream:  $2^{31}-1$  pseudo-random bit sequence
- Nearly ideal interconnect performance; indistinguishable from PG.
- Error-free operation
  - SNR (Q) = 12.9 for pattern generator alone, 12.4 after chip-to-chip interconnect



Raw pattern generator

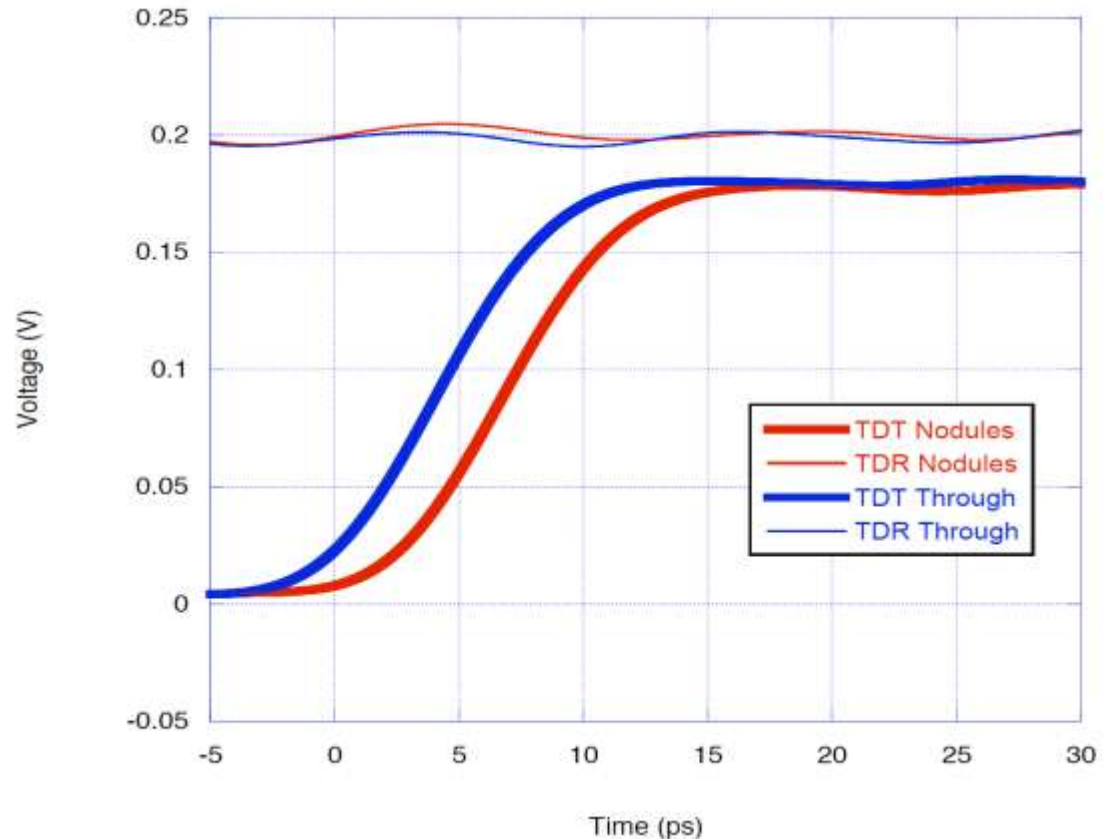


50  $\mu$ m  
GSG eye



# QP Time-Domain Performance

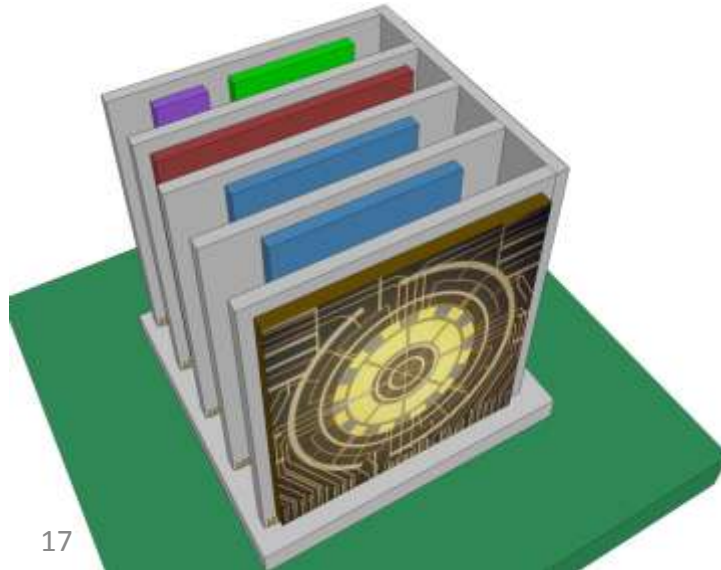
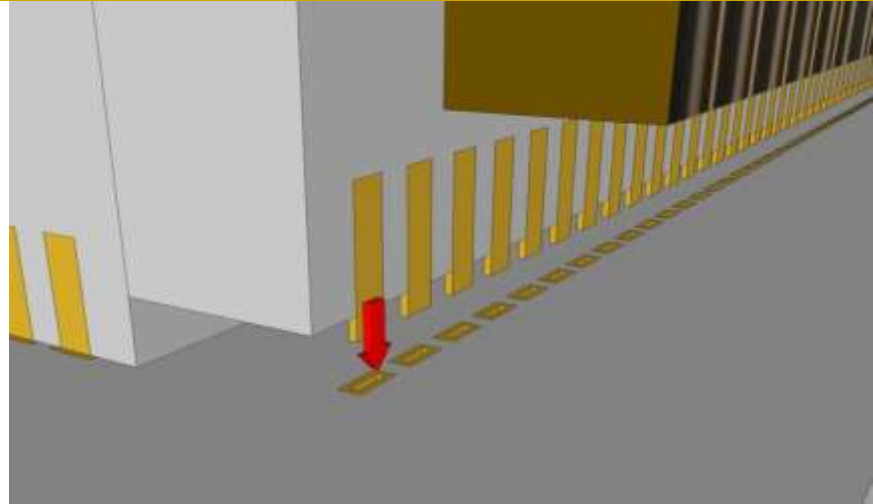
- Single-ended GSG CPW configuration
- Picosecond Pulse Labs 4022 TDR pulse enhancement module: < 9 ps risetime
- Total delay including probe pads, launcher: 7 ps (820  $\mu\text{m}$  length)
- Delay due to QP nodules: 2.7 ps



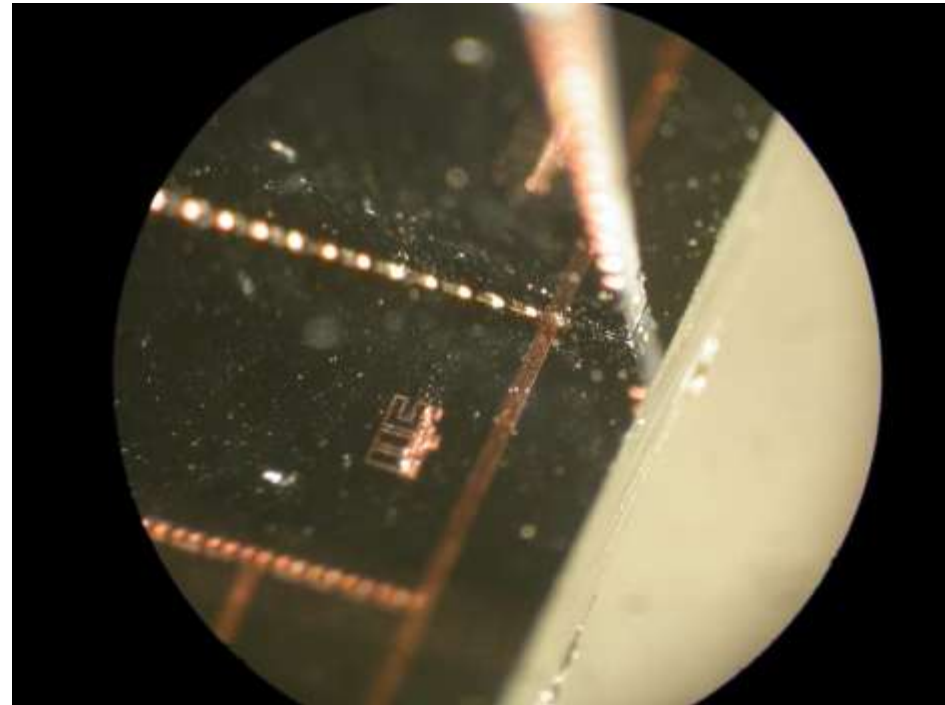
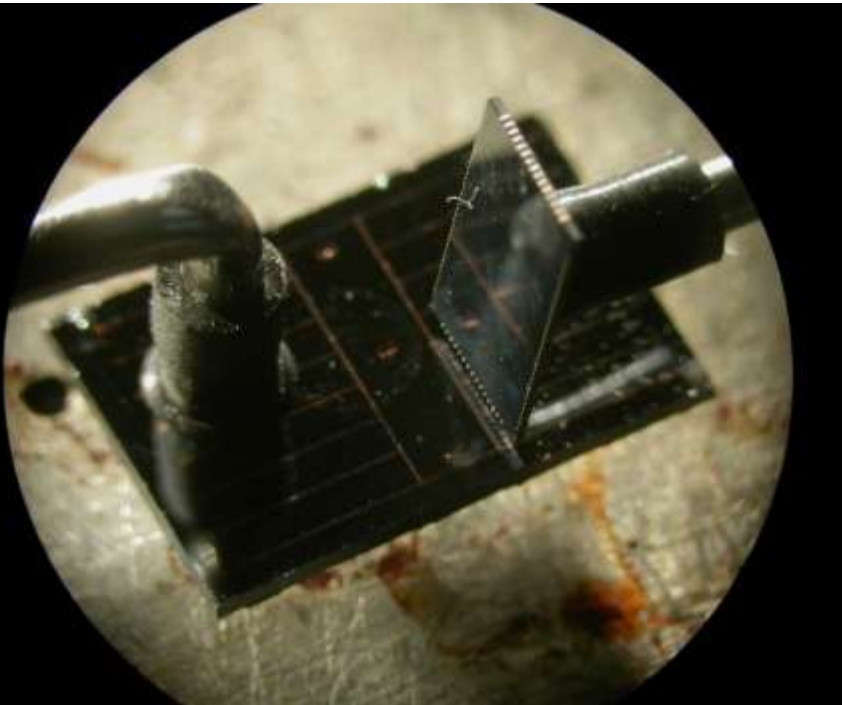
100  $\mu\text{m}$  nodule compared with pads/launcher, GSG

# “3D-QP” and “Interposers”

- QP can enable multiple 3D configurations
- 3D-QP retains many advantages of 2D-QP
- “Quilting” interposers can decrease form-factor
- Systems benefit from QP without having to redesign chips



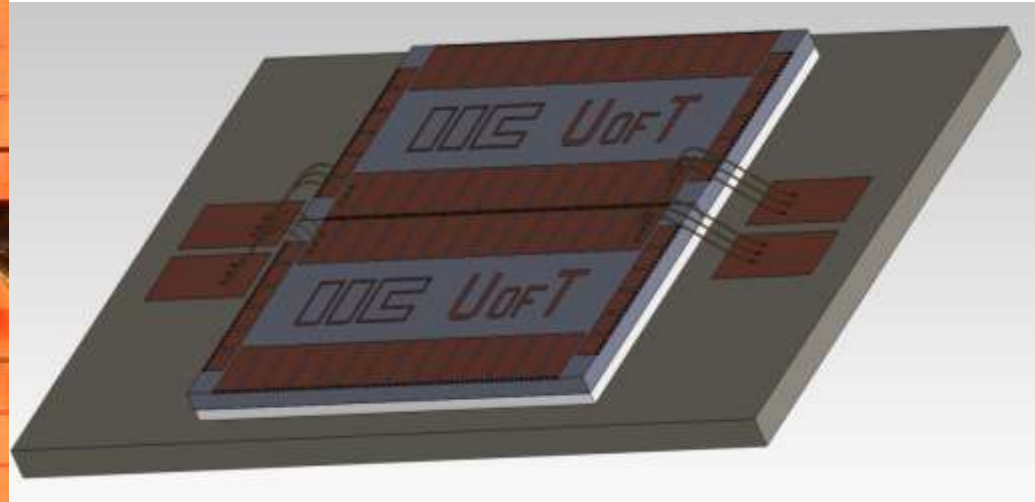
# 3D Si QP Test Articles



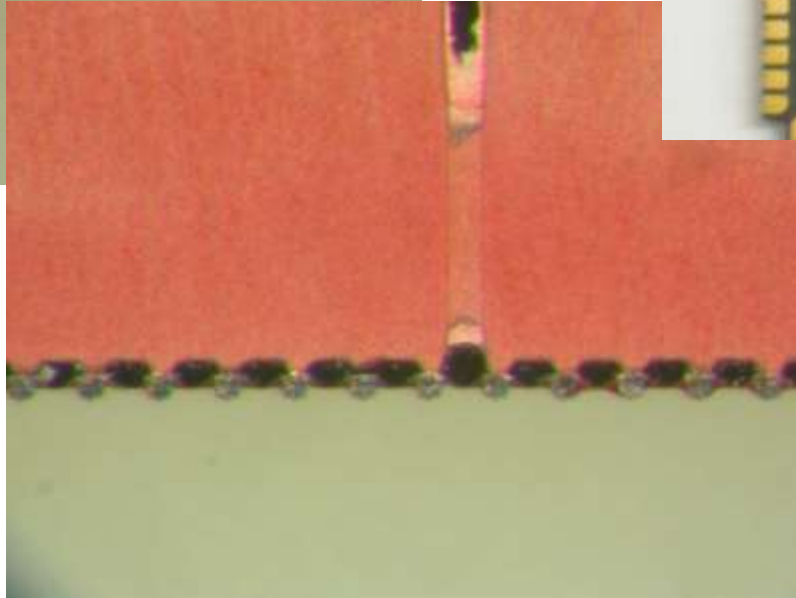
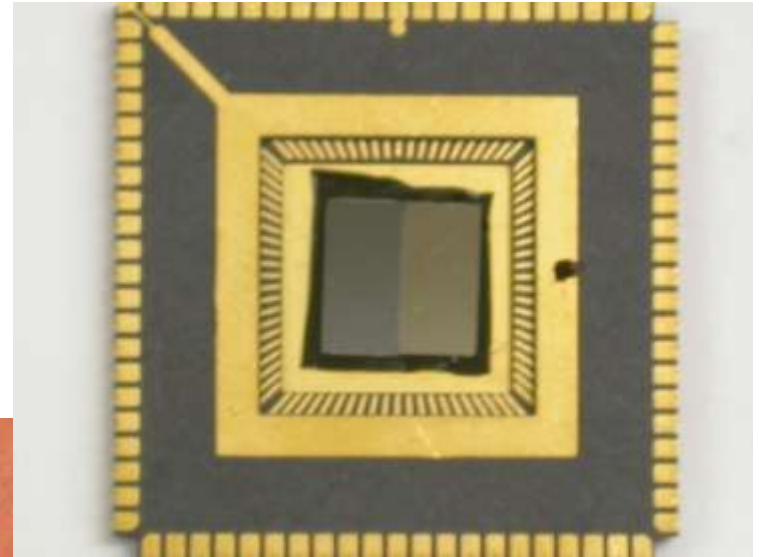
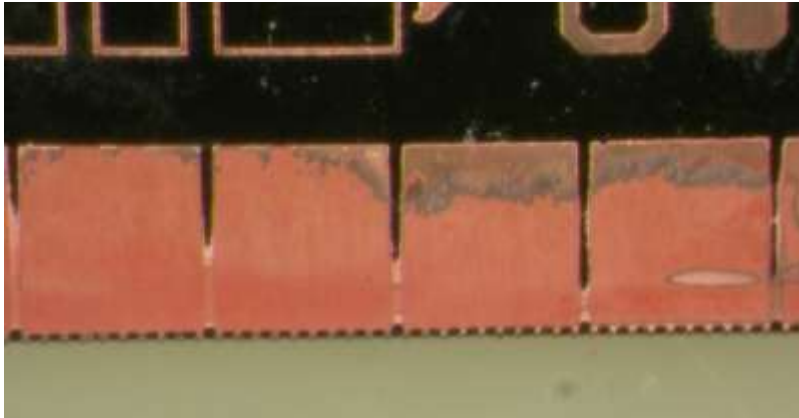
# Advantages of Quilt Packaging

- Optimized integration of disparate materials and process technologies (Si, GaN, GaAs, AlN, more)
- Chip partitioning for optimal yield/functionality
- Increased cross-sectional area vs. WBs, bumps
- Better thermal management & failure modes compared to WB
- Reduced design time due to applicability of current 2-D tools, design re-use
- IP flexibility, security

# Original intent-test using wirebonds

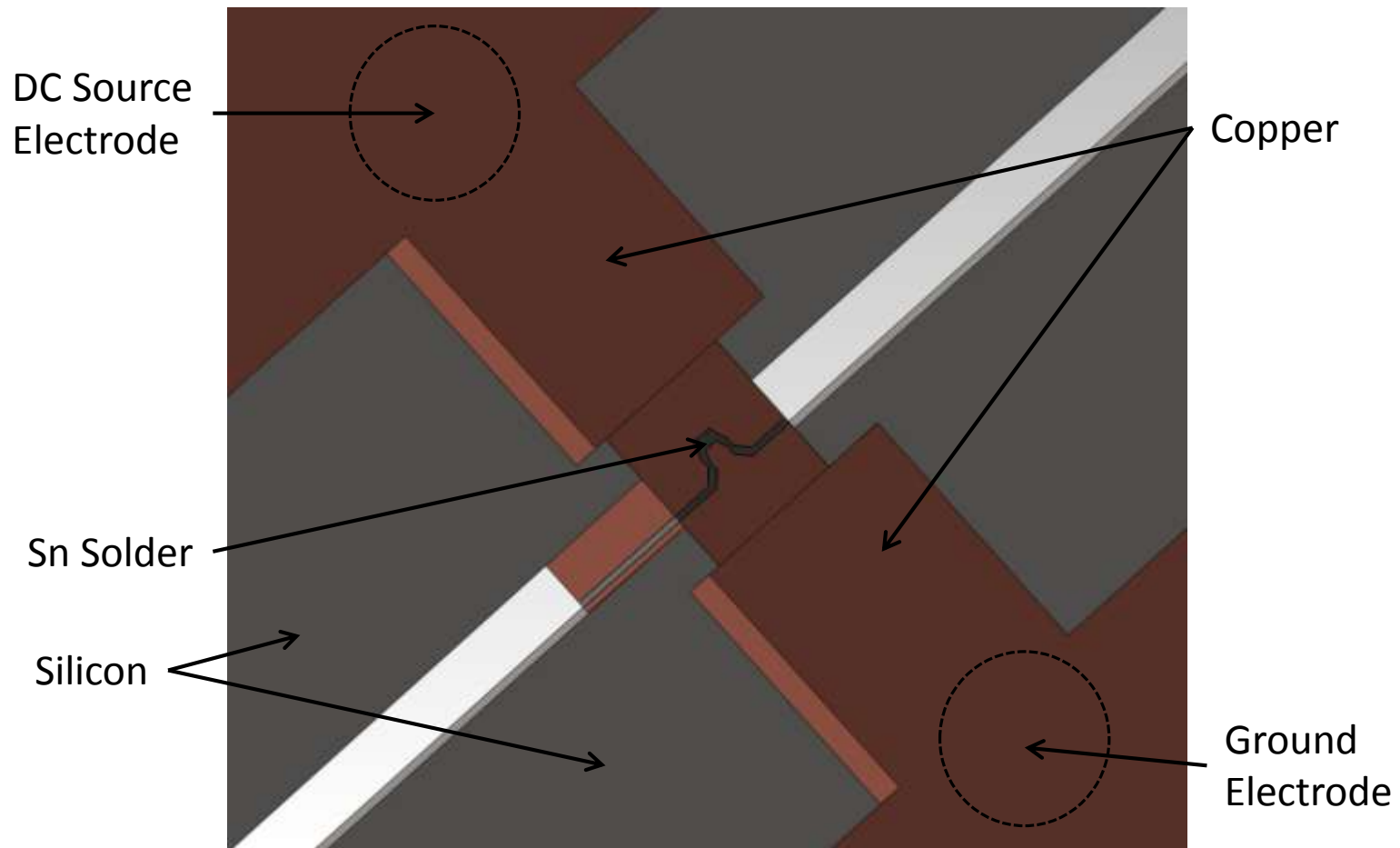


# Early test articles--couldn't wirebond, had to probe directly



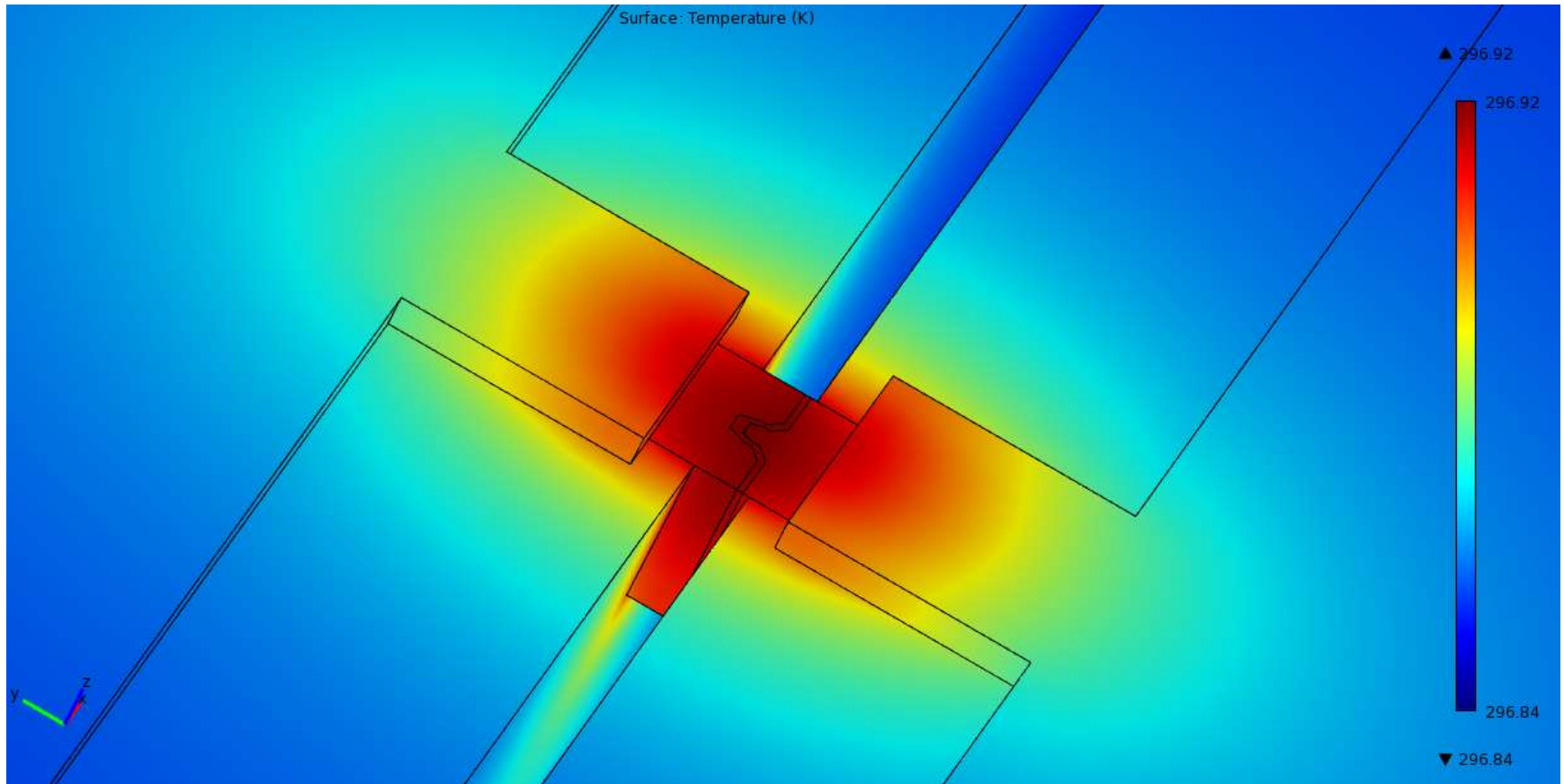


# Joule heating simulation through nodules interconnect (setup)



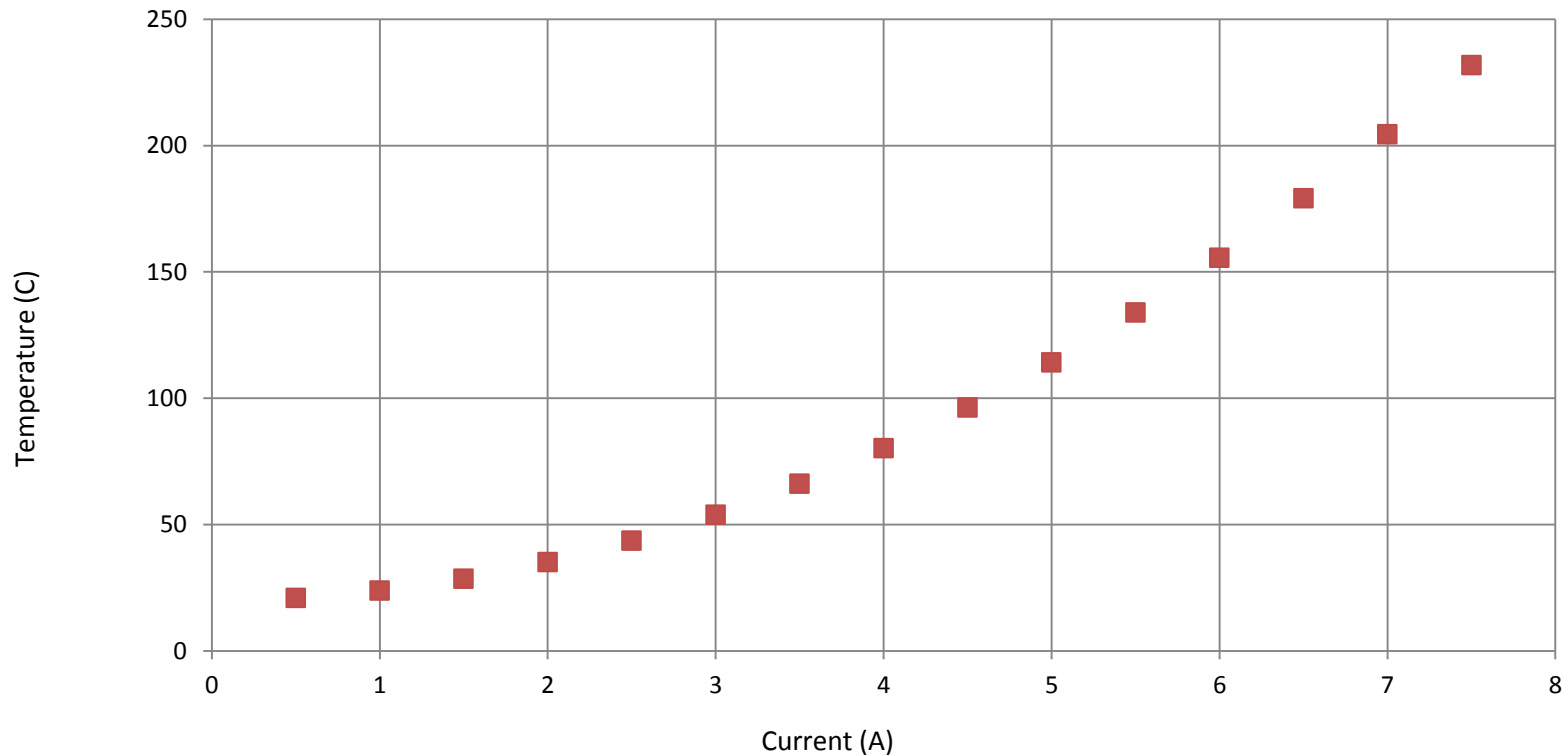


# Joule heating simulation through quilted interconnect (no showstoppers)

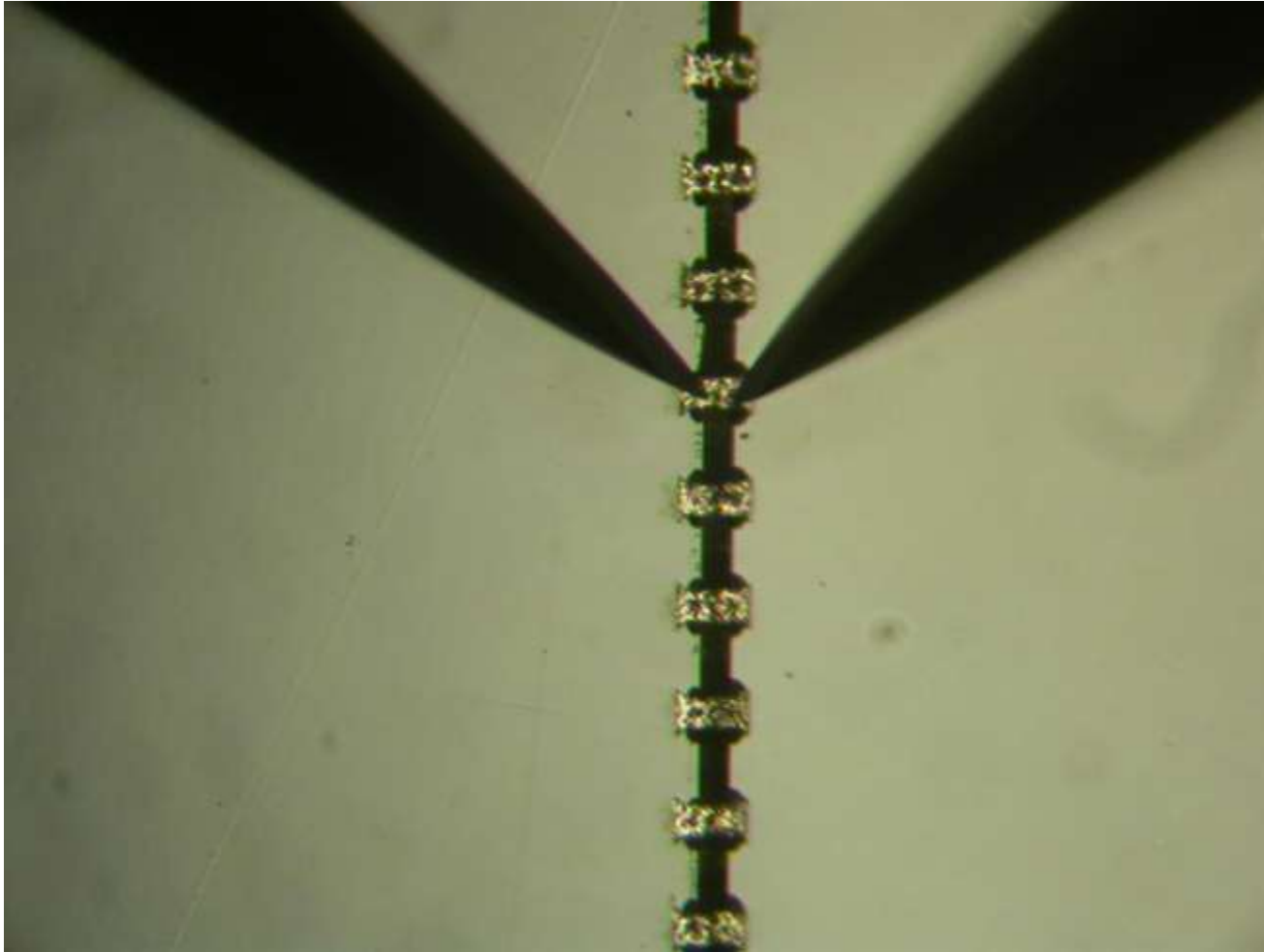


# Simulations don't include heatsink, nodule size 30 $\mu\text{m}$ X 20 $\mu\text{m}$

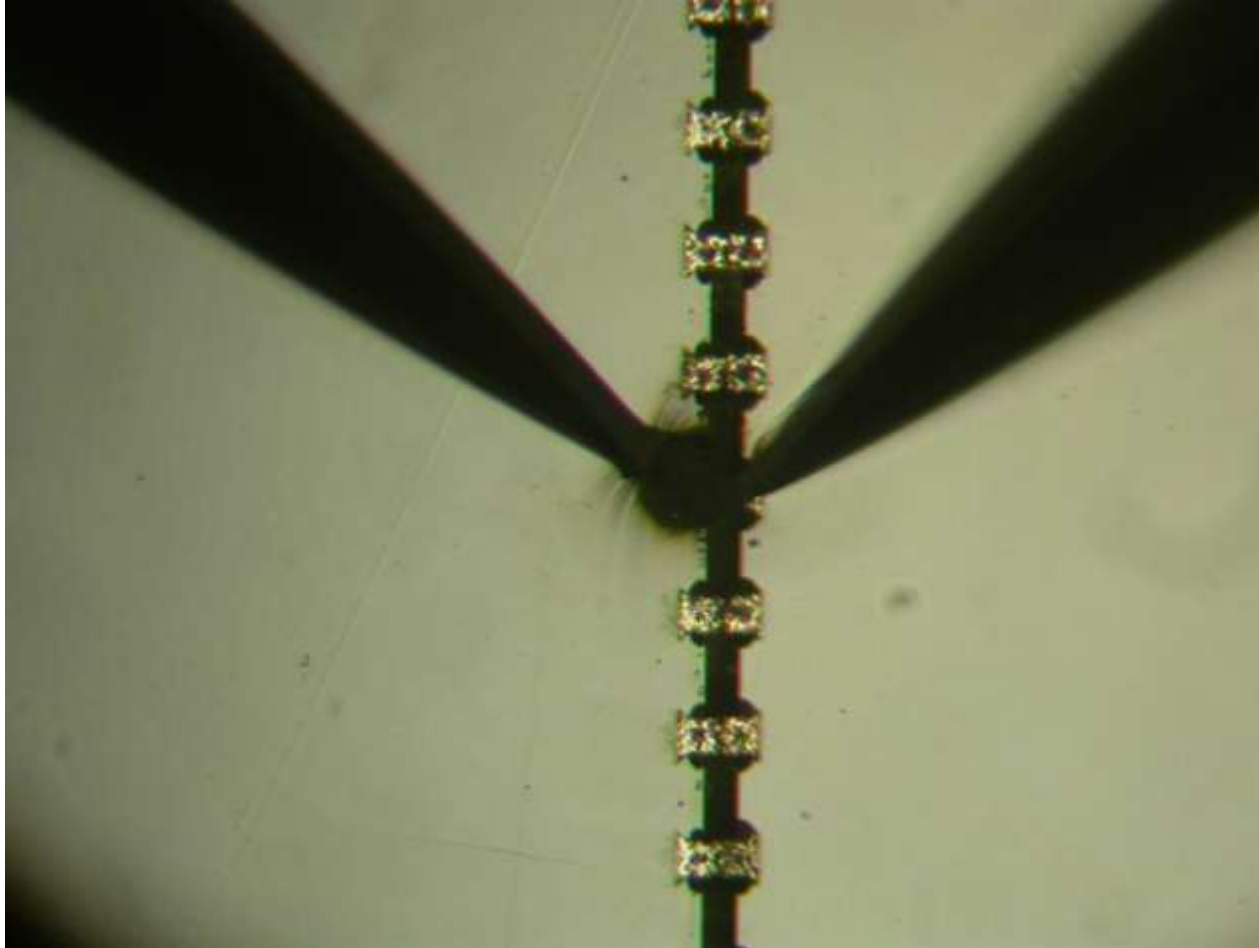
Temperature Across Quilted Nodule (30 $\mu\text{m}$  x 25  $\mu\text{m}$  cross area) w/ Metal 1 From Applied Current



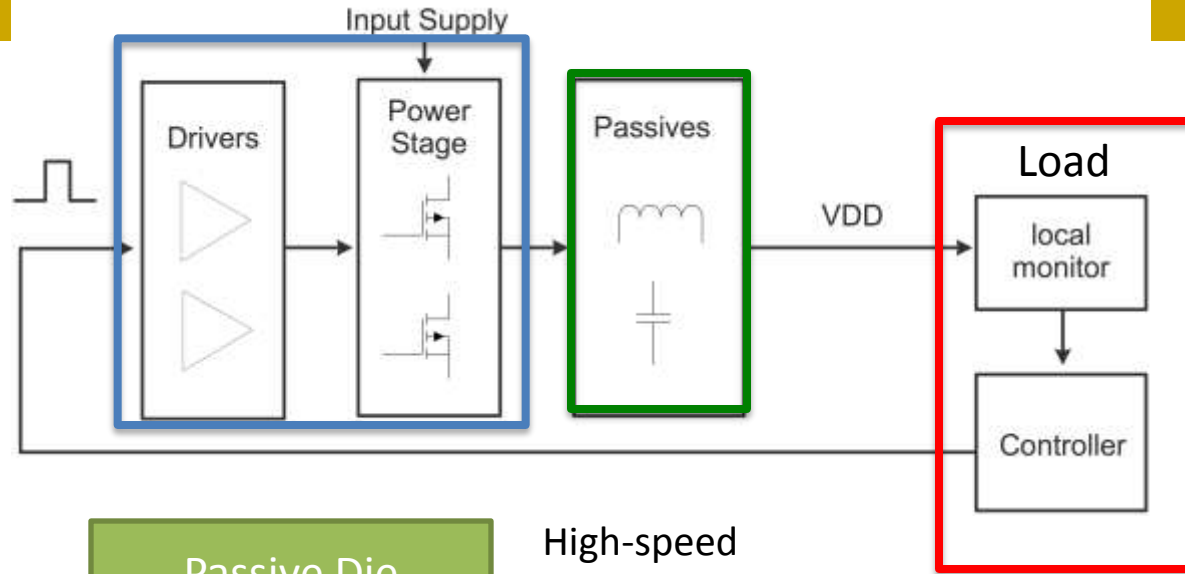
# Si QP Max current probe test (before), nodule size 30 $\mu\text{m}$ X 20 $\mu\text{m}$



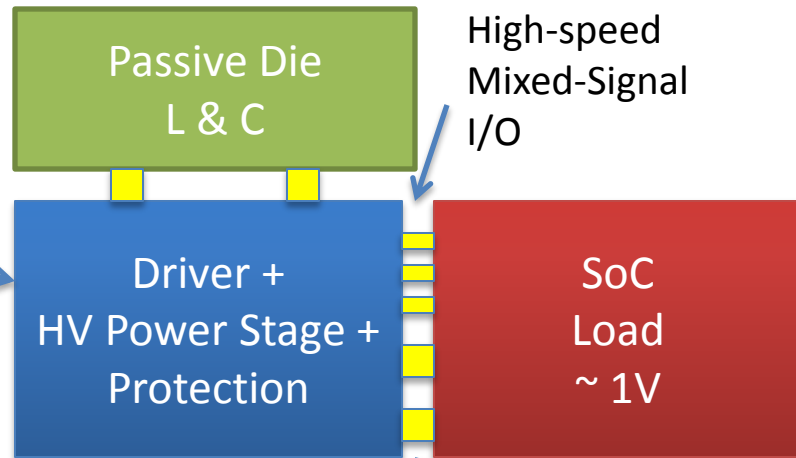
# Si QP Max current test--probes fail before nodules (~2.25A)



# Potential Uses of QP In Power Electronics



Low-cost  
Power-optimized  
12V BCD

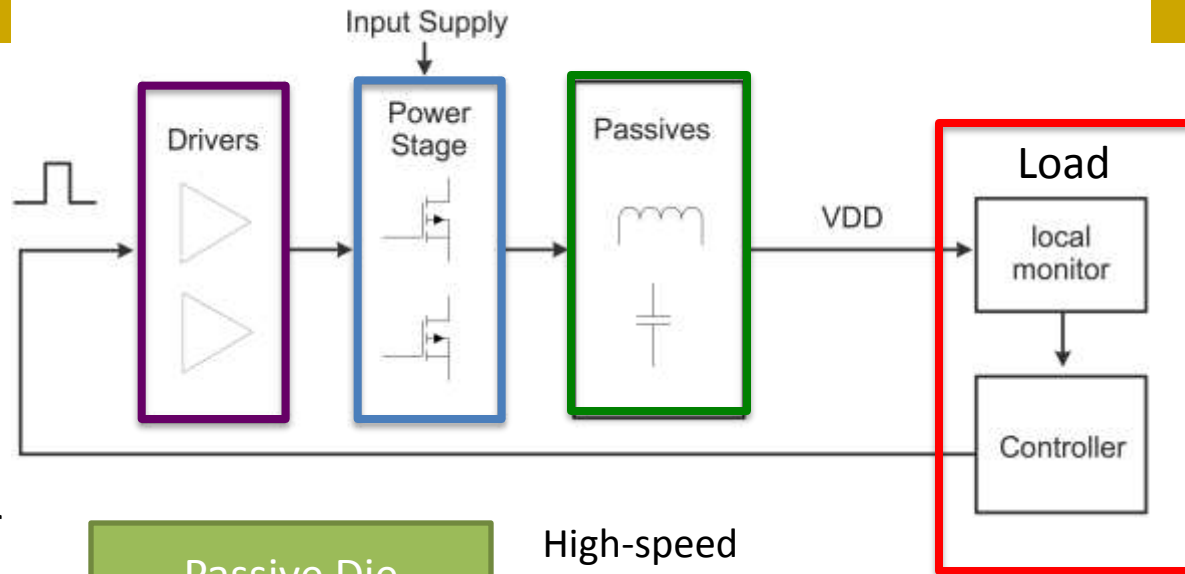


Digital optimized  
CMOS

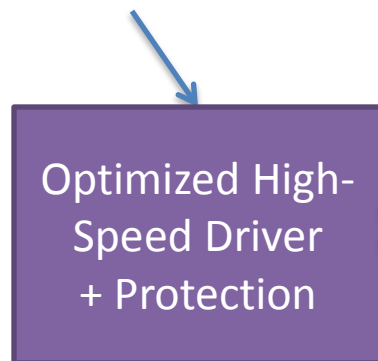
**High-current, low ESR, ESL  
Power Connection**



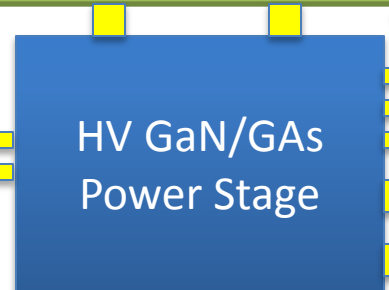
# Potential Uses of QP In Power Electronics



Low-cost CMOS or BCD



High-speed Mixed-Signal I/O

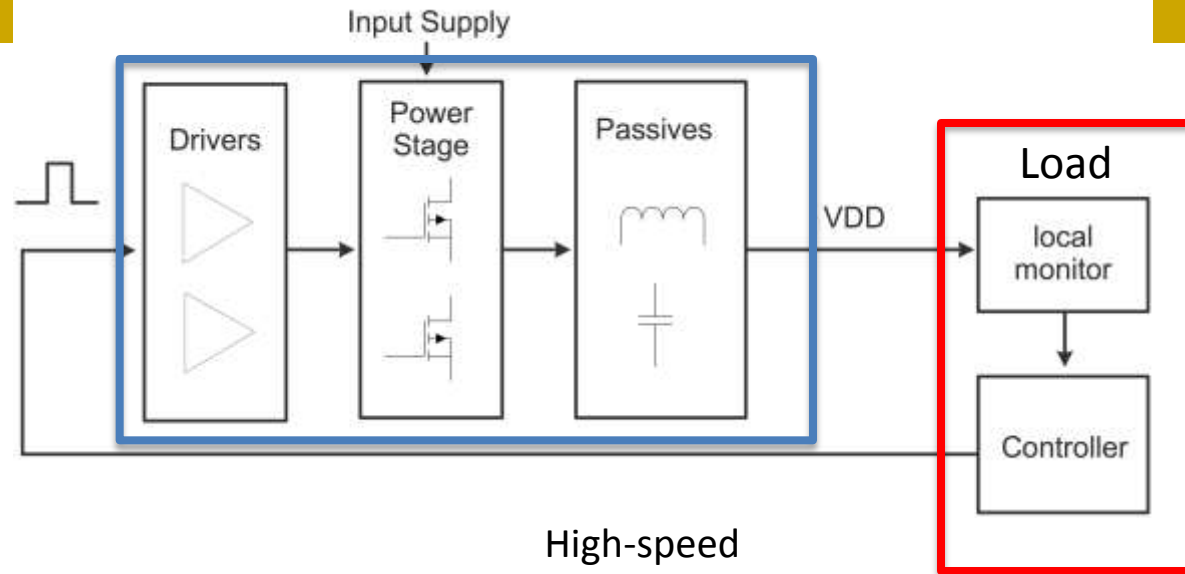


Digital optimized CMOS

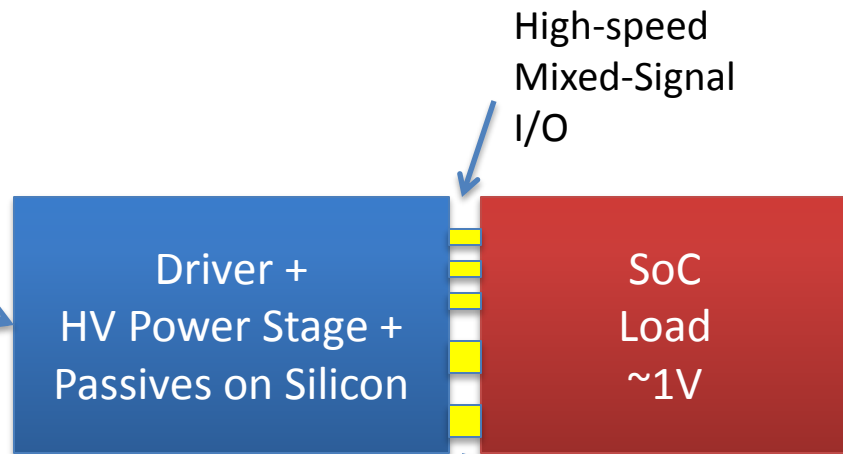
**High-current, low ESR, ESL Power Connection**



# Potential Uses of QP In Power Electronics



BCD or  
GaN/GAs with  
On-chip drivers



**High-current, low ESR, ESL  
Power Connection**





# Future Work

- Thermal cycle/shock testing of preliminary “quilts” (ongoing)
- Completion of DC-DC converter demonstration (3-chip quilt w/QP Si interposer---ongoing)
- GaN QP (just starting)
- Chip architectures & partitioning for power
- Other?---Specific partner applications, etc.

# Thank You!

For More Information Contact:

Jason Kulick

[jason.kulick@indianaic.com](mailto:jason.kulick@indianaic.com)

(574) 217-4612

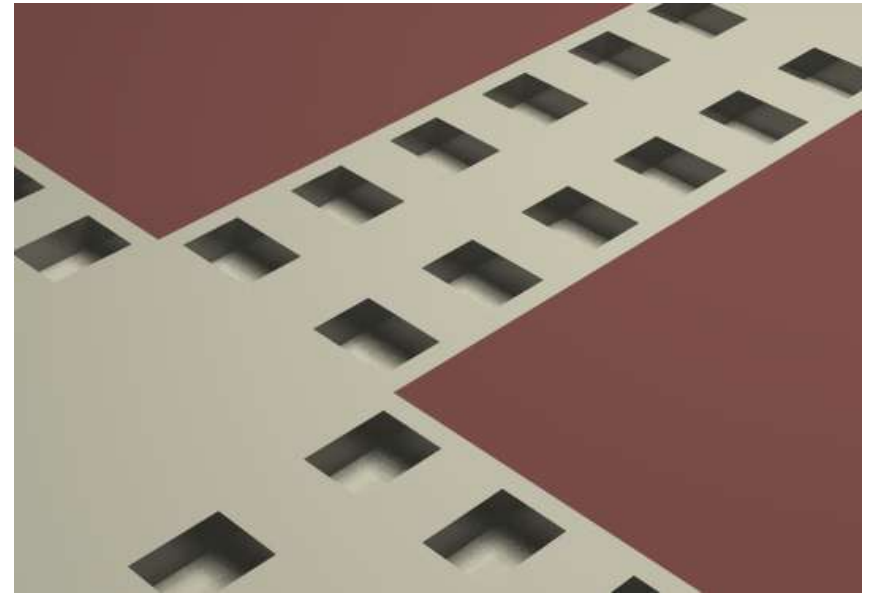
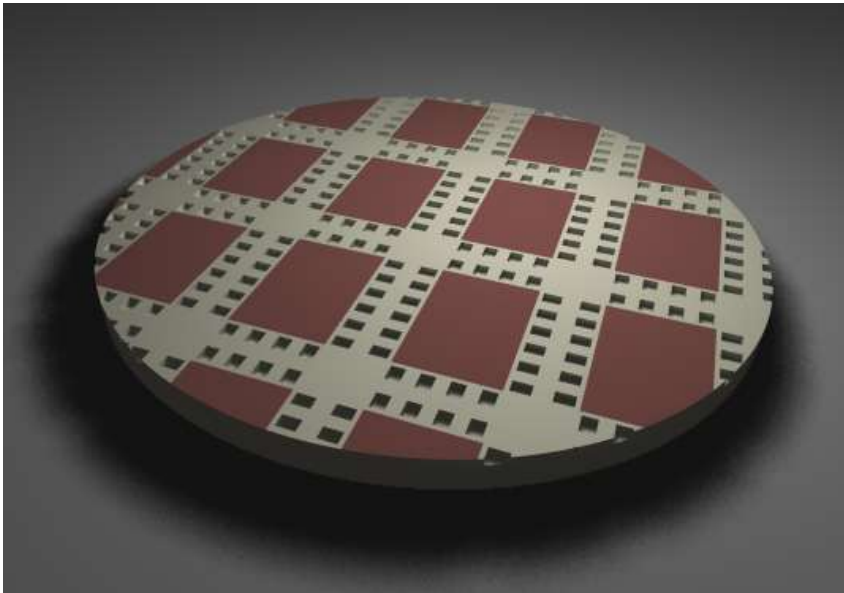
And/or visit:

[www.indianaic.com](http://www.indianaic.com)

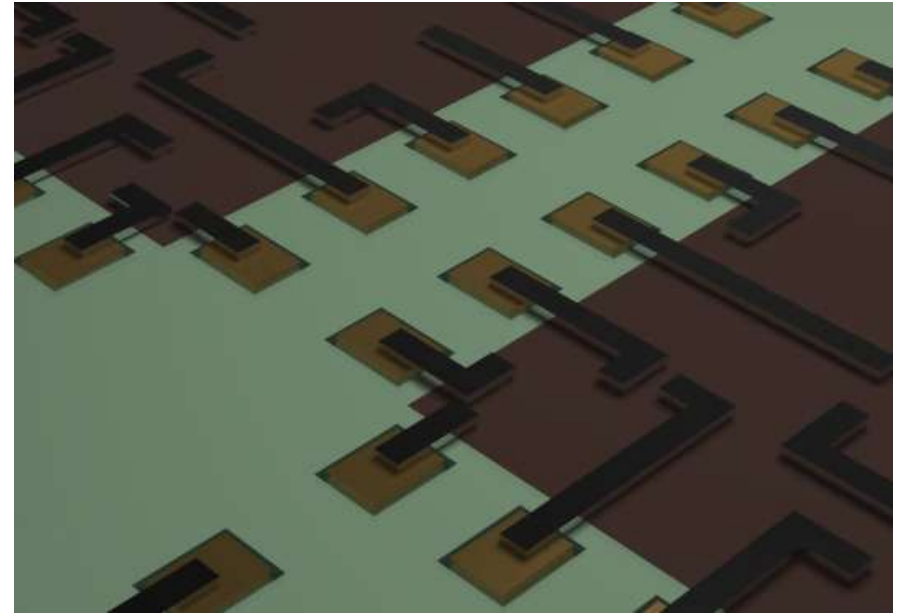
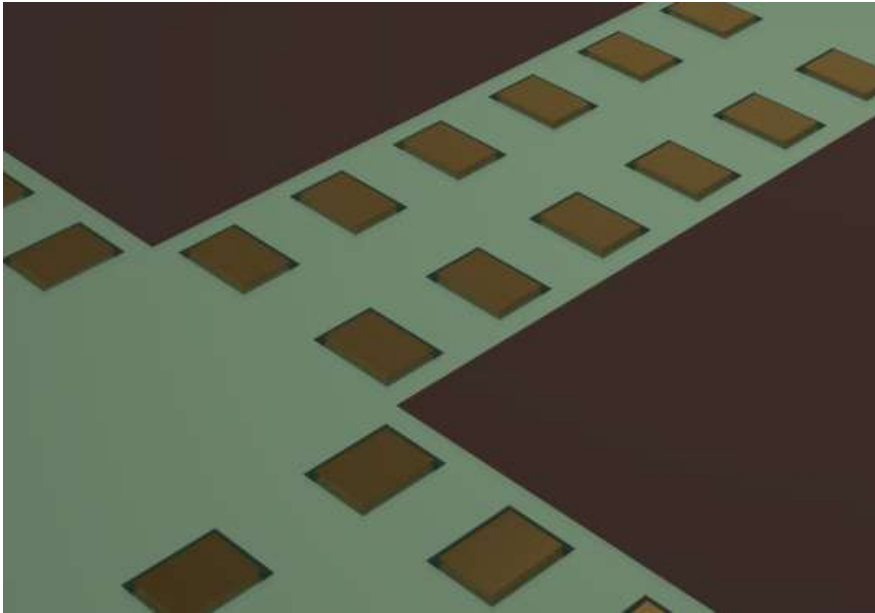
# QP Fabrication Process Flow Overview

- Very similar to “via-middle” TSV process
- Utilizes industry-standard tools & processes
- At least 2 additional mask steps
  - Nodule definition
  - Separation
- Most unique feature is dry etch step for singulation
- After assembly, handle as if “normal” chip

# QP Fabrication-Nodule Definition



# QP Fabrication- Nodule Metallization



# QP Fabrication-Die Singulation

